

FDC645N

N-Channel PowerTrench® MOSFET

General Description

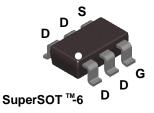
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{\text{DS(ON)}}$ and fast switching speed.

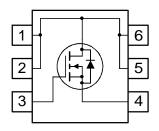
Applications

• DC/DC converter

Features

- 5.5 A, 30 V. $R_{DS(ON)} = 30 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 26 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- Low gate charge (13 nC typical)
- High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	5.5	Α
	- Pulsed		20	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J , T_{STG}	Operating and Storage Junction Tem	perature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

•	Device Marking	Device	Reel Size	Tape width	Quantity
	.645	FDC645N	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1		l	l	l
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \ \ V_{GS} = 0 \text{ V}$			1	μА
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.8	1.4	2	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		- 4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 6.2 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}, T_J = 125^{\circ}\text{C}$		25 23 34	30 26 48	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	20			Α
g FS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 5.5 \text{ A}$		33		S
Dvnamio	Characteristics	•				
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		1460		pF
Coss	Output Capacitance	f = 1.0 MHz		227		pF
C _{rss}	Reverse Transfer Capacitance	1		96		pF
Switchir	g Characteristics (Note 2)			•	•	
t _{d(on)}	Turn-On Delay Time	$V_{DS} = 15 \text{ V}, I_{D} = 1 \text{ A},$		8	16	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
t _{d(off)}	Turn-Off Delay Time	1		35	56	ns
t _f	Turn-Off Fall Time	1		7	14	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 6.2 \text{ A},$		13	21	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		3.6		nC
Q_{gd}	Gate-Drain Charge	7		3.6		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings	•	•	•	•
l _s	Maximum Continuous Drain-Source				1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 1.3 \text{ A}$ (Note 2)		0.7	1.2	V

Notes:

- R_{0JA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design.
 - a. 78°C/W when mounted on a 1in^2 pad of 2oz copper on FR-4 board.
 - b. 156°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$

Typical Characteristics

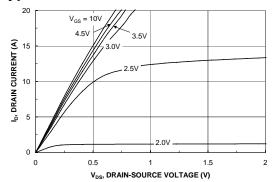
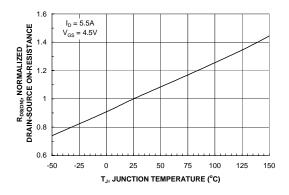


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



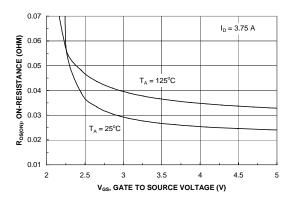
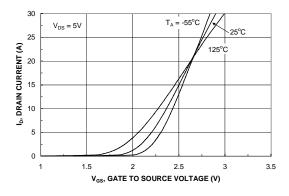


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



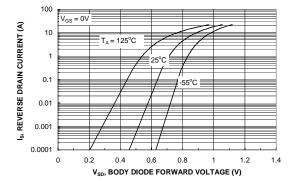
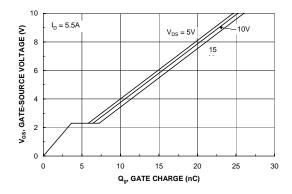


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



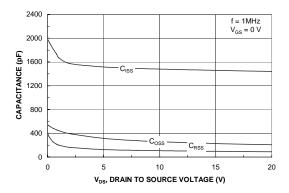
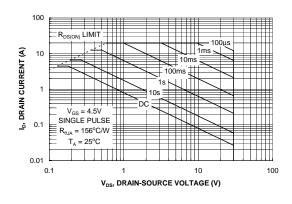


Figure 7. Gate Charge Characteristics.





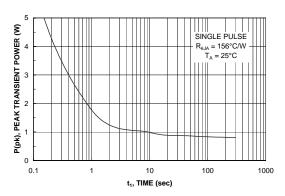


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

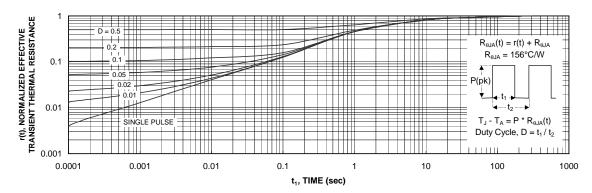
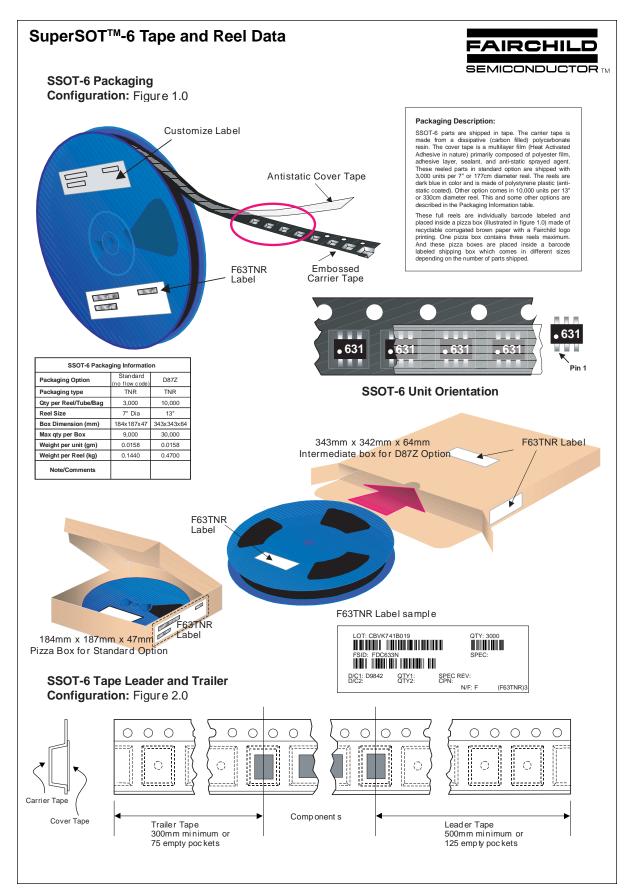


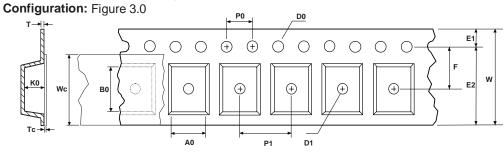
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.





SSOT-6 Embossed Carrier Tape



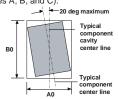


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

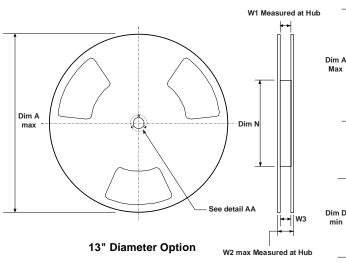


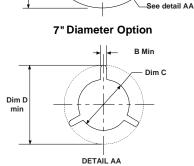
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SSOT-6 Reel Configuration: Figure 4.0



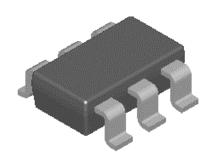


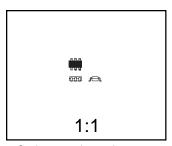
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT[™]-6 Package Dimensions



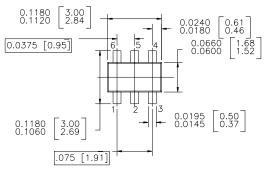
SuperSOT™-6 (FS PKG Code 31, 33)

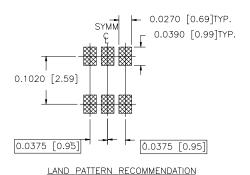




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

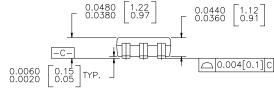
Part Weight per unit (gram): 0.0158

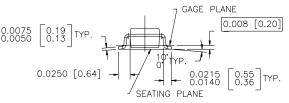




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NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$

SUPER SOT 6 LEADS

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DenseTrench™	HiSeC™	QS™	TinyLogic™
DOME™	ISOPLANAR™	QT Optoelectronics™	UHC TM
EcoSPARK™	LittleFET™	Quiet Series™	UltraFET®
E ² CMOS TM	MicroFET™	SILENT SWITCHER ®	VCX^{TM}
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